9. The method according to claim 8, wherein the metal layer is provided by Light Induced Plating.

10. A method according to any of the above claims, further comprising:
    - providing a dielectric layer on the textured surface of the silicon substrate;
    - forming openings through the dielectric layer at predetermined locations where the patterned metal silicide layer needs to be formed.

11. A method according to claim 10 wherein the metal layer is at least provided at the location of the predetermined openings.

12. The method according to claims 10 or 11, wherein forming openings through the dielectric layer comprises forming the openings by means of laser ablation.

13. The method according to ~~any of the previous claims~~ claim 10, further comprising providing a doped region at the textured surface before providing the dielectric layer, thereby forming a p-n junction.

14. The method according to any of the previous claims, further comprising performing a (second) plating step, thereby forming another metal layer on top of the metal silicide layer.

15. Use of a method according to any of the previous claims in a process for fabricating a photovoltaic cell, wherein the dielectric layer is a surface passivation layer.

16. Use of a method according to any of the previous claims in a process for fabricating a photovoltaic cell, wherein the dielectric layer is an antireflection coating.